High-Speed USB 2.0 (480 Mbps) DPST Switch

The NLAS7213 is a DPST switch optimized for high-speed USB 2.0 applications within portable systems. It features ultra-low off capacitance, $C_{OFF} = 3.0 \text{ pF}$ (typ), and a bandwidth above 1118 MHz. It is optimized for applications that use a single USB interface connector to route multiple signal types. The C_{ON} and R_{ON} of both switches are suitably low to allow the NLAS7213 to pass any speed USB data or audio signals going to a moderately resistive terminal such as an external headset.

The NLAS7213 is protected on all pins with 8 kV Human Body Model ESD protection. It is offered in a 1.5 x 1.5 mm UQFN8 package.

Features

- R_{ON} : 8.5 Ω Max @ V_{CC} = 3.3 V
- C_{OFF} : 3.0 pF Typ @ V_{CC} = 3.3 V
- V_{CC} Operating Range: 1.65 V to 4.5 V
- > 1118 MHz Bandwidth
- OVT up to 5.25 V on D+/D- Pins
- 1.5 x 1.5 x 0.55 mm UQFN8
- 8 kV ESD Protection on All Pins
- This is a Pb–Free Device

Typical Applications

- High Speed USB 2.0 Data
- Mobile Phones
- Portable Devices

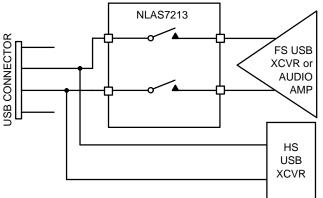
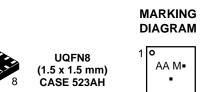


Figure 1. Application Diagram



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(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

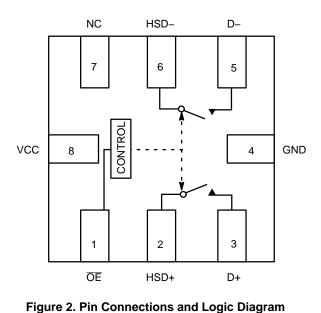


Table 1. PIN DESCRIPTION

Pin	Function
ŌĒ	Control Input Select Line
HSD+, HSD–, D+, D–	Data Ports

Table 2. TRUTH TABLE

ŌĒ	Both Switches
1	OPEN
0	CLOSED

(Top View)

MAXIMUM RATINGS

Symbol	Pins	Parameter	Value	Unit
V _{CC}	V _{CC}	Positive DC Supply Voltage	-0.5 to +4.6	V
V _{IS}	HSD+, HSD-	Analog Signal Voltage	-0.5 to V _{CC} + 0.3	V
	D+, D–	Γ	-0.5 to +5.25	
V _{IN}	ŌĒ	Control Input Voltage	-0.5 to +4.6	V
I _{CC}	V _{CC}	Positive DC Supply Current	50	mA
Т _S		Storage Temperature	-65 to +150	°C
I _{IS_CON}	HSD+, HSD–, D+, D–	Analog Signal Continuous Current–Closed Switch	±300	mA
I _{IS_PK}	HSD+, HSD–, D+, D–	Analog Signal Continuous Current 10% Duty Cycle	±500	mA
I _{IN}	ŌĒ	Control Input Current	±20	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Pins	Parameter	Min	Max	Unit
V _{CC}		Positive DC Supply Voltage	1.65	4.5	V
V _{IS}	HSD+, HSD-	Analog Signal Voltage	GND	V _{CC}	V
	D+, D–		GND	4.5	
V _{IN}	ŌĒ	Digital Select Input Voltage	GND	V _{CC}	V
T _A		Operating Temperature Range	-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ESD PROTECTION

Symbol	Parameter	Value	Unit
ESD	Human Body Model – All Pins	8.0	kV

DC ELECTRICAL CHARACTERISTICS

CONTROL INPUT (Typical: T = 25°C, V_{CC} = 3.3 V)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
V _{IH}	ŌĒ	Control Input HIGH Voltage		2.7 3.3 4.2	1.3 1.3 1.4	_	_	V
V _{IL}	ŌĒ	Control Input LOW Voltage		2.7 3.3 4.2	_	_	0.4 0.4 0.4	V
I _{IN}	ŌĒ	Control Input Leakage Current	V _{IS} = GND	1.65 – 4.5	-	-	±1.0	μΑ

SUPPLY CURRENT AND LEAKAGE (Typical: T = 25°C, V_{CC} = 3.3 V, V_{IN} = V_{CC} or GND)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
I _{CC}	V _{CC}	Quiescent Supply Current	$V_{IS} = V_{CC}$ or GND; $I_D = 0$ A	1.65 – 4.5	-	-	1.0	μΑ
I _{NC(OFF)}	HSD+, HSD-	OFF State Leakage Current	$V_{COM} = 3.6 \text{ V}, V_{NC} = 1.0 \text{ V}$	1.65 – 4.5	-	-	±1.0	μΑ
I _{OFF}		Power OFF Leakage Current	$V_{IS} = GND$	0	-	-	±1.0	μΑ

ON RESISTANCE (Typical: T = 25°C, V_{CC} = 3.3 V)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
R _{ON}		On-Resistance	$I_{ON} = -8 \text{ mA}$ $V_{IS} = 0 \text{ to } 0.4 \text{ V}$	2.7 3.3 4.2	_	9.0 8.0 7.2	9.5 8.5 7.5	Ω
R _{FLAT}		On–Resistance Flatness	$I_{ON} = -8 \text{ mA}$ $V_{IS} = 0 \text{ to } 0.4 \text{ V}$	2.7 3.3 4.2	_	0.8 0.5 0.3	-	Ω
ΔR _{ON}		On–Resistance Matching	$I_{ON} = -8 \text{ mA}$ $V_{IS} = 0 \text{ to } 0.4 \text{ V}$	2.7 3.3 4.2	-	0.07 0.07 0.04	-	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

TIMING/FREQUENCY (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 Ω , C_L = 35 pF, f = 1 MHz)

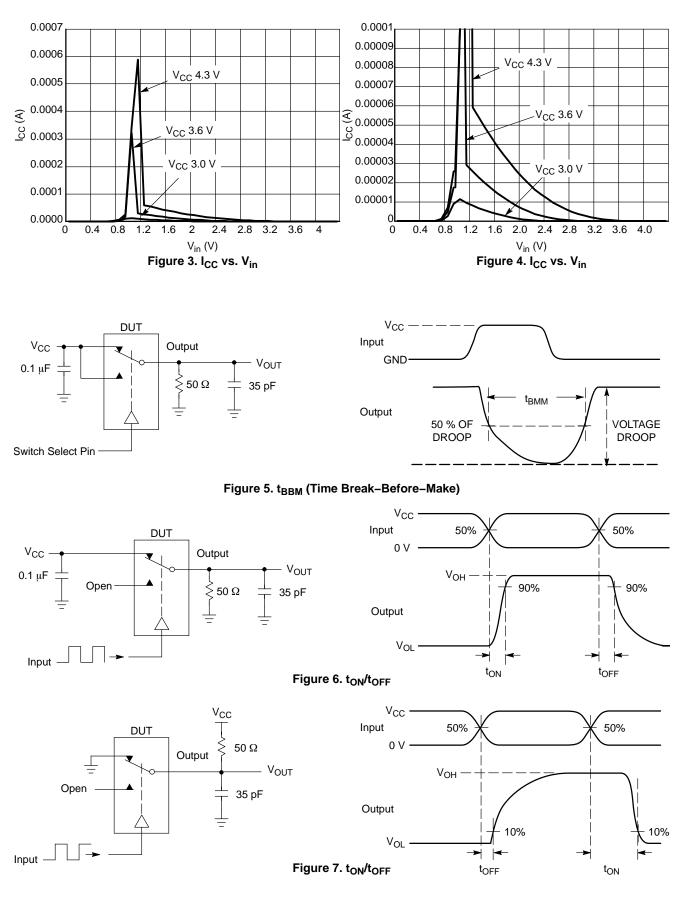
					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
t _{ON}		Turn-ON Time (Figures 6, 7)		1.65 – 4.5	-	13.0	30.0	ns
t _{OFF}		Turn–OFF Time (Figures 6, 7)		1.65 – 4.5	-	12.0	25.0	ns
t _{PD}		Propagation Delay		1.65 – 4.5	-	0.25	-	ns
BW		-3 dB Bandwidth	C _L = 5 pF	1.65 – 4.5	-	1118	-	MHz

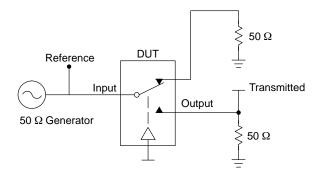
ISOLATION (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 $\Omega,$ C_L = 5 pF)

				–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	Min	Тур	Max	Unit
O _{IRR}	Open	OFF-Isolation	f = 240 MHz	-	-20	-	dB
X _{TALK}	HSD+, HSD-	Non–Adjacent Channel Crosstalk	f = 240 MHz	-	-30	-	dB

CAPACITANCE (Typical: T = 25°C, V_{CC} = 3.3 V, f = 1 MHz)

				–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	Min	Тур	Max	Unit
C _{IN}	ŌĒ	Control Pin Input Capacitance	$V_{IS} = 3.3 V_{p-p}, V_{CC} = 0 V$	-	2.0	-	pF
C _{ON}	I/O to GND	ON Capacitance	$V_{IS} = 3.3 V_{p-p}, \overline{OE} = 0 V$	-	3.0	-	pF
C _{OFF}	I/O to GND	OFF Capacitance	$V_{IS} = 3.3 V_{p-p}, \overline{OE} = 3.3 V$	-	3.0	-	pF





Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log}\left(\frac{V_{OUT}}{V_{IN}}\right) \text{for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log}\left(\frac{V_{OUT}}{V_{IN}}\right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \text{ to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL} V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

> Figure 8. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

NLAS7213

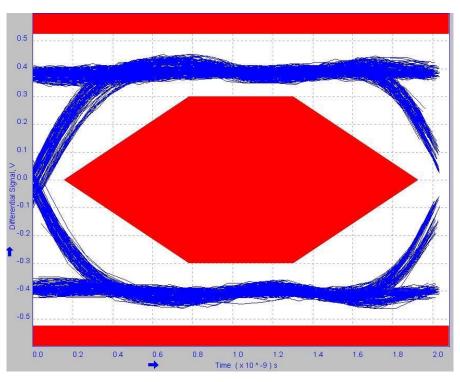


Figure 9. Signal Quality

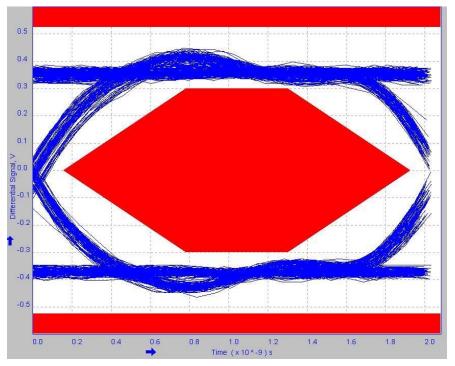


Figure 10. Near End Eye Diagram

Near End Test Data						Max
Std.	Consecutive Jitter Range	-44.80	76.30	ps	–200 ps	+200 ps
	Paired JK Jitter Range	-63.59	56.33	ps		
	Paired KJ Jitter Range	-44.15	45.68	ps		
NO	Consecutive Jitter Range	-58.40	90.58	ps	–200 ps	+200 ps
	Paired JK Jitter Range	-65.90	70.64	ps		
	Paired KJ Jitter Range	-52.43	55.14	ps		

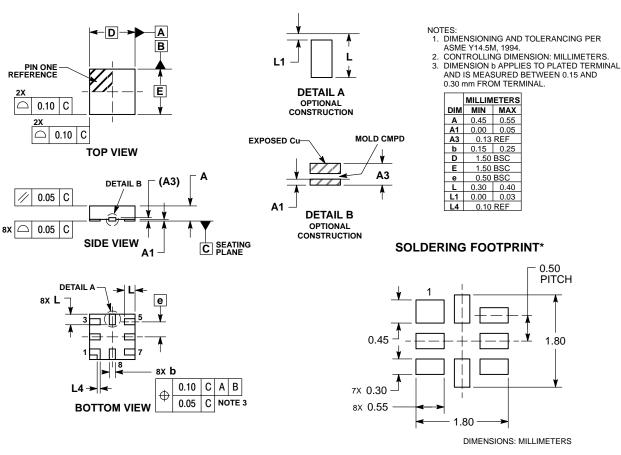
ORDERING INFORMATION

Device	Package	Shipping†
NLAS7213MUTBG	UQFN8 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

UQFN8, 1.5x1.5, 0.5P CASE 523AH ISSUE O



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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